ALP SEMI	HA & ON CONDU	<b>MEGA</b> CTOR			30V N-Ch	AO3480 annel MOSFET
General Descrip	otion			Product Sum	mary	
The AO3480 combined technology with a location of the extremely low $R_{DS(O)}$ load switch or in PW	backage to pr e is suitable f	rovide		30V 5.7A < 26.5mΩ < 32mΩ < 48mΩ		
RoHS and Halogen	-Free Complia	nt				Green
Absolute Maximum	Top View	DT23 Bottom Vi	G G	oted	G	
Parameter			Symbol		timum	Units
Drain-Source Voltage			V <sub>DS</sub>		30	V
Gate-Source Voltage			V <sub>GS</sub>	±	12	V
Continuous Drain Current	T <sub>A</sub> =25°C T <sub>A</sub> =70°C		- I <sub>D</sub>	<u> </u>	A	
Pulsed Drain Current	С		I <sub>DM</sub>			
Power Dissipation <sup>B</sup> $T_A=25^{\circ}C$ $P_D$			-P <sub>D</sub>	1.4 W		
			T <sub>J</sub> , T <sub>STG</sub>	-55	°C	
		~	0. 010			
Thermal Characteris	tics					
Pa	rameter		Symbol	Тур	Max	Units
Maximum Junction-to		t ≤ 10s	R	70	90	°C/W
Maximum Junction-to	-Ambient AD	Steady-State	R <sub>θJA</sub>	100	125	°C/W

Maximum Junction-to-Ambient AD

Maximum Junction-to-Lead

Steady-State

 $R_{\theta JL}$ 

63

80

°C/W



### Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise noted)

Symbol	Parameter	Conditions		Min	Тур	Max	Units
STATIC I	PARAMETERS						
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	I <sub>D</sub> =250μA, V <sub>GS</sub> =0V		30			V
1	Zero Gate Voltage Drain Current	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V			1	^	
I <sub>DSS</sub>	Zero Gale Voltage Drain Current		TJ=55°C			5	μA
I <sub>GSS</sub>	Gate-Body leakage current	$V_{DS}$ =0V, $V_{GS}$ = ±12V				100	nA
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{DS}=V_{GS} I_{D}=250 \mu A$		0.65	1.05	1.45	V
I <sub>D(ON)</sub>	On state drain current	V <sub>GS</sub> =4.5V, V <sub>DS</sub> =5V		30			А
		V <sub>GS</sub> =10V, I <sub>D</sub> =5.7A			18	26.5	mΩ
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance		T <sub>J</sub> =125°C		28	38	11152
	Static Drain-Source On-Resistance	V <sub>GS</sub> =4.5V, I <sub>D</sub> =5A			19	32	mΩ
		V <sub>GS</sub> =2.5V, I <sub>D</sub> =3A			24	48	mΩ
9 <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> =5V, I <sub>D</sub> =5.7A			33		S
V <sub>SD</sub>	Diode Forward Voltage	I <sub>S</sub> =1A,V <sub>GS</sub> =0V			0.7	1	V
ls	Maximum Body-Diode Continuous Cur	rent			2	А	
DYNAMI	C PARAMETERS						
C <sub>iss</sub>	Input Capacitance				630		pF
C <sub>oss</sub>	Output Capacitance	V <sub>GS</sub> =0V, V <sub>DS</sub> =15V, f=	=1MHz		75		pF
C <sub>rss</sub>	Reverse Transfer Capacitance				50		pF
R <sub>g</sub>	Gate resistance	V <sub>GS</sub> =0V, V <sub>DS</sub> =0V, f=1	MHz	1.5	3	4.5	Ω
SWITCH	NG PARAMETERS						
Qg	Total Gate Charge				6	10	nC
Q <sub>gs</sub>	Gate Source Charge	$V_{GS}$ =4.5V, $V_{DS}$ =15V,	I <sub>D</sub> =5.7A		1.3		nC
$Q_{gd}$	Gate Drain Charge				1.8		nC
t <sub>D(on)</sub>	Turn-On DelayTime				3		ns
t <sub>r</sub>	Turn-On Rise Time	$V_{GS}$ =10V, $V_{DS}$ =15V, R <sub>L</sub> =2.6 $\Omega$ , R <sub>GEN</sub> =3 $\Omega$			2.5		ns
t <sub>D(off)</sub>	Turn-Off DelayTime				25		ns
t <sub>f</sub>	Turn-Off Fall Time				4		ns
t <sub>rr</sub>	Body Diode Reverse Recovery Time	I <sub>F</sub> =5.7A, dI/dt=100A/µ	us		8.5		ns
Q <sub>rr</sub>	Body Diode Reverse Recovery Charge	e I <sub>F</sub> =5.7A, dI/dt=100A/	us		2.6		nC

A. The value of R<sub>8JA</sub> is measured with the device mounted on 1in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with T<sub>A</sub> =25° C. The

value in any given application depends on the user's specific board design. B. The power dissipation  $P_D$  is based on  $T_{J(MAX)}=150^{\circ}$  C, using  $\leq 10$  s junction-to-ambient thermal resistance. C. Repetitive rating, pulse width limited by junction temperature  $T_{J(MAX)}=150^{\circ}$  C. Ratings are based on low frequency and duty cycles to keep initialT<sub>1</sub>=25° C.

D. The  $R_{\theta JA}$  is the sum of the thermal impedence from junction to lead  $R_{\theta JL}$  and lead to ambient.

E. The static characteristics in Figures 1 to 6 are obtained using <300µs pulses, duty cycle 0.5% max.

F. These curves are based on the junction-to-ambient thermal impedence which is measured with the device mounted on  $1n^2$  FR-4 board with 20z. Copper, assuming a maximum junction temperature of  $T_{J(MAX)}$ =150° C. The SOA curve provides a single pulse rating.

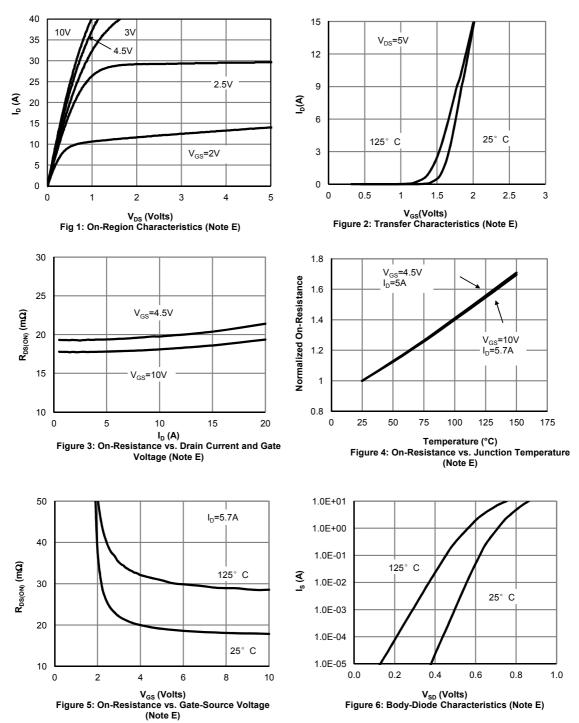
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AO3480



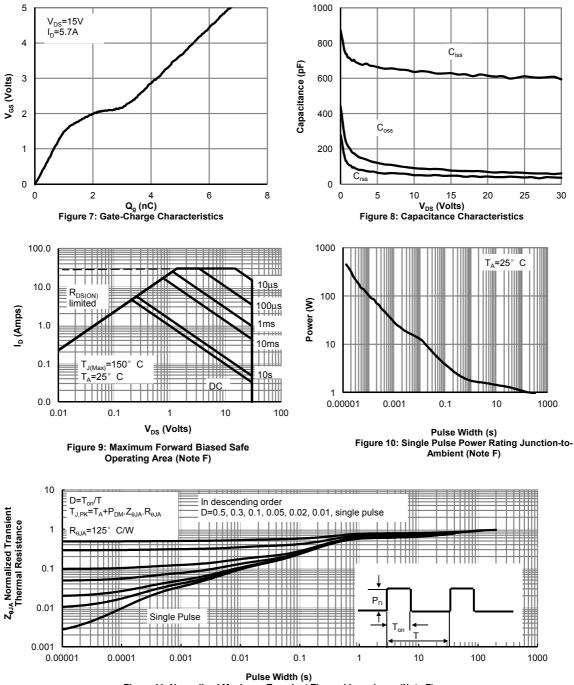
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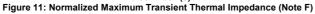
SEMICONDUCTOR





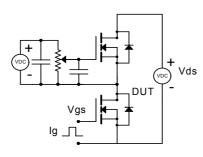
### TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

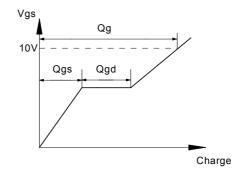




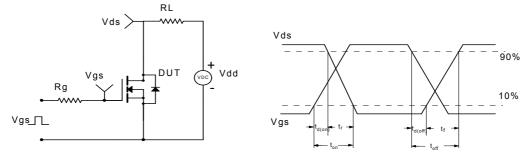


### Gate Charge Test Circuit & Waveform

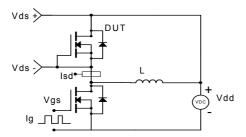


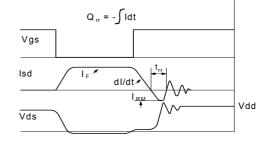


Resistive Switching Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms

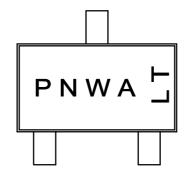






Document No.	PD-02361
Version	А
Title	AO3480 Marking Description

### SOT-23 PACKAGE MARKING DESCRIPTION



Green product

### NOTE:

- Р - Package and product type
- Ν - Last digital of product number
- W - Week code
- A Assembly location code L&T Assembly lot code

PART NO.	DESCRIPTION	CODE (PN)
AO3480	Green product	CN

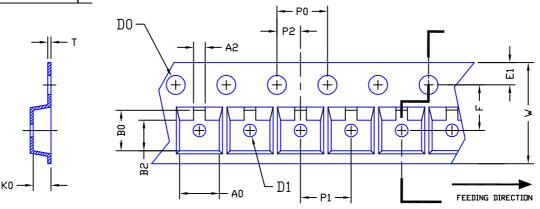
	<b>ALPHA &amp; ON</b> SEMICONDU	<u>IEGA</u> CTOR			Document No Version	. PO-00001 L
				l		
		SOT23 PA	CKAGE (			
		30123 17		JOTEINE		
RECOMMENDED LAND PATTERN $\frac{1}{4} = \frac{1}{4} $	E1				0.25	mm
SYMBOLS    DIMENSIONS IN MILLIMETERS      MIN    NOM    MAX    M      A    0.85     1.25    0.0      A1    0.00     0.13    0.0      A2    0.70    1.00    1.15    0.0      b    0.30    0.40    0.50    0.0      c    0.08    0.13    0.20    0.0      D    2.80    2.90    3.10    0.1      E    2.60    2.80    3.00    0.1      E1    1.40    1.60    1.80    0.0      0.95    0.80				3]0.10mm]		
SYMBOLS    MIN    NOM    MAX    M      A    0.85     1.25    0.0      A1    0.00     0.13    0.0      A2    0.70    1.00    1.15    0.0      b    0.30    0.40    0.50    0.0      c    0.08    0.13    0.20    0.0      D    2.80    2.90    3.10    0.1      E    2.60    2.80    3.00    0.1      E1    1.40    1.60    1.80    0.0      e    0.95 BSC	ECOMMENDED LAND PATTER	N				
UNIT mm		TN II TT- una contra	$ \begin{array}{c c} & A \\ \hline A \\ A1 \\ ( \\ A2 \\ ( \\ A2 \\ ( \\ C \\ C$	IIN      NOM        .85	MAX      MIN        1.25      0.03        0.13      0.00        1.15      0.02        0.50      0.01        0.20      0.00        3.10      0.11        3.00      0.10        1.80      0.05        0.60      0.01	3       0.049        0       0.005        8      0.039      0.045        2      0.016      0.020        3      0.005      0.008        0      0.114      0.122        2      0.110      0.118        5      0.063      0.071        0.037 BSC      0.075 BSC
	L	JNIT: mm				

- 2. TOLERANCE ±0.100 mm (4 mil) UNLESS OTHERWISE SPECIFIED.
- DIMENSION L IS MEASURED IN GAUGE PLANE.
  CONTROLLING DIMENSION IS MILLIMETER. CONVERTED INCH DIMENSIONS
- ARE NOT NECESSARILY EXACT.
- 5. ALL DIMENSIONS ARE IN MILLIMETERS.





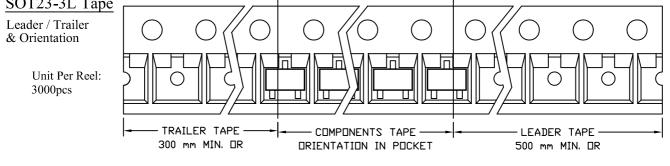
# SOT23-3L Carrier Tape



UNIT: MM

PACKAGE	A0	B0	К0	DO	D1	W	E1	F	P0	P1	P2	Т	A2	B5
SDT23-3L (8 mm)	3.05-3.40	3.00-3.38	1.20- 1.47	1.55 ±0.05	1.00 ±0.25	8.00 ±0.30	1.75 ±0.10	3.50 ±0.05	4.00 ±0.10	4.00 ±0.10	2.00 ±0.05	0.18 -0.25	0.84-1.24	2.29-2.69

#### SOT23-3L Reel - W1 - S G ż > -| |-- v UNIT: MM TAPE SIZE REEL SIZE W W1 Н К S G М Ν R V ø54.00 ±0.50 ø13.00 +0.50 -0.20 2.00 ±0.50 ø178 ø178.00 9.00 11.40 10.60 ø9.00 5.00 18.00 8 mm ±1.00 ±0.30 ±1.00 SOT23-3L Tape





This AOS product reliability report summarizes the qualification result for AO3480. Accelerated environmental tests are performed on a specific sample size, and then followed by electrical test at end point. Review of final electrical test result confirms that AO3480 passes AOS quality and reliability requirements. The released product will be categorized by the process family and be routine monitored for continuously improving the product quality.

Test Item	Test Condition	Time Point	Total Sample Size	Number of Failures	Reference Standard
HTGB	Temp = 150°C , Vgs=100% of Vgsmax	168 / 500 / 1000 hours	924 pcs	0	JESD22-A108
HTRB	Temp = 150°C, Vds=80% of Vdsmax	168 / 500 / 1000 hours	924 pcs	0	JESD22-A108
Precondition (Note A)	168hr 85°C / 85%RH + 3 cycle reflow@260°C (MSL 1)	-	5082 pcs	0	JESD22-A113
HAST	130°C ,85%RH, 33.3 psia, Vds = 80% of Vdsmax	96 hours	924 pcs	0	JESD22-A110
H3TRB	85°C , 85%RH, Vds = 80% of Vdsmax	1000 hours	693 pcs	0	JESD22-A101
Autoclave	121°C , 29.7psia, RH=100%	96 hours	924 pcs	0	JESD22-A102
Temperature Cycle	-65°C to 150°C, air to air,	1000 cycles	924 pcs	0	JESD22-A104
HTSL	Temp = 150°C	1000 hours	924 pcs	0	JESD22-A103
Power Cycling	∆ Tj = 100°C	15000 cycles	693 pcs	0	AEC Q101

## I. Reliability Stress Test Summary and Results

**Note:** The reliability data presents total of available generic data up to the published date. Note A: MSL (Moisture Sensitivity Level) 1 based on J-STD-020

# **II. Reliability Evaluation**

# FIT rate (per billion): 1.91 MTTF = 59839 years

The presentation of FIT rate for the individual product reliability is restricted by the actual burn-in sample size. Failure Rate Determination is based on JEDEC Standard JESD 85. FIT means one failure per billion hours.

Failure Rate =  $Chi^2 \times 10^9 / [2 (N) (H) (Af)] = 1.91$ **MTTF =**  $10^9$  / FIT = 59839 vears Chi<sup>2</sup> = Chi Squared Distribution, determined by the number of failures and confidence interval **N** = Total Number of units from burn-in tests **H** = Duration of burn-in testing Af = Acceleration Factor from Test to Use Conditions (Ea = 0.7eV and Tuse =  $55^{\circ}C$ ) Acceleration Factor [Af] = Exp [Ea / k (1/Tj u - 1/Tj s)] **Acceleration Factor ratio list:** 85 deg C 100 deg C 55 deg C 70 deg C 115 deg C 130 deg C 150 deg C 259 87 32 13 5.64 2.59 Af 1

Tj s = Stressed junction temperature in degree (Kelvin), K = C+273.16

**Tj u** =The use junction temperature in degree (Kelvin), K = C+273.16

 $\mathbf{k}$  = Boltzmann's constant, 8.617164 X 10<sup>-5</sup> eV / K

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